

Important notice

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Kind regards,

Team Nexperia



PDTB113/123/143/114EQA series

50 V, 500 mA PNP resistor-equipped transistors

Rev. 1 — 30 March 2016

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

Table 1. Product overview

Type number	R1	R2	Package NXP	NPN complement
PDTB113EQA	1 k Ω	1 k Ω	DFN1010D-3 (SOT1215)	PDTD113EQA
PDTB123EQA	2.2 k Ω	2.2 k Ω		PDTD123EQA
PDTB143EQA	4.7 k Ω	4.7 k Ω		PDTD143EQA
PDTB114EQA	10 k Ω	10 k Ω		PDTD114EQA

1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- $\pm 10\%$ resistor ratio tolerance
- Simplifies circuit design
- Reduces component count
- Reduced pick and place costs
- Low package height of 0.37 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

1.3 Applications

- Digital applications
- Cost saving alternative for BC807/BC817 series in digital applications
- Controlling IC inputs
- Switching loads

1.4 Quick reference data

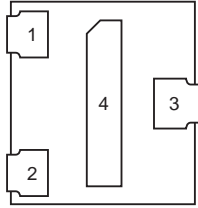
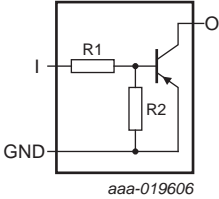
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-500	mA



2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 <p>Transparent top view</p>	 <p>aaa-019606</p>
2	GND	GND (emitter)		
3	O	output (collector)		
4	O	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTB113EQA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body: 1.1 × 1.0 × 0.37 mm	SOT1215
PDTB123EQA			
PDTB143EQA			
PDTB114EQA			

4. Marking

Table 5. Marking codes

Type number	Marking code
PDTB113EQA	00 00 01
PDTB123EQA	01 01 01
PDTB143EQA	01 01 11
PDTB114EQA	01 10 11

4.1 Binary marking code description

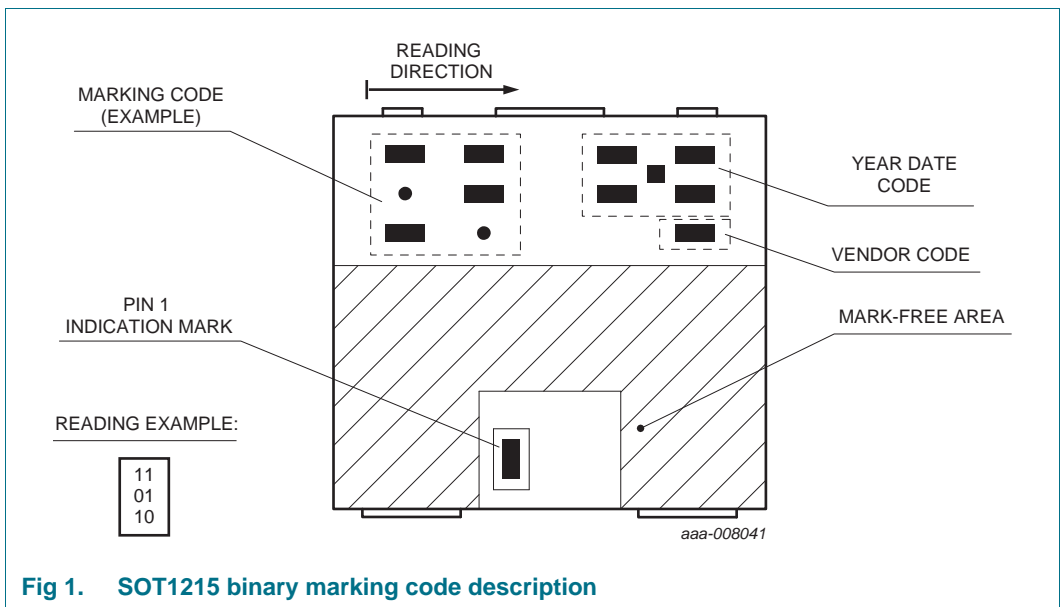


Fig 1. SOT1215 binary marking code description

5. Limiting values

Table 6. Limiting values

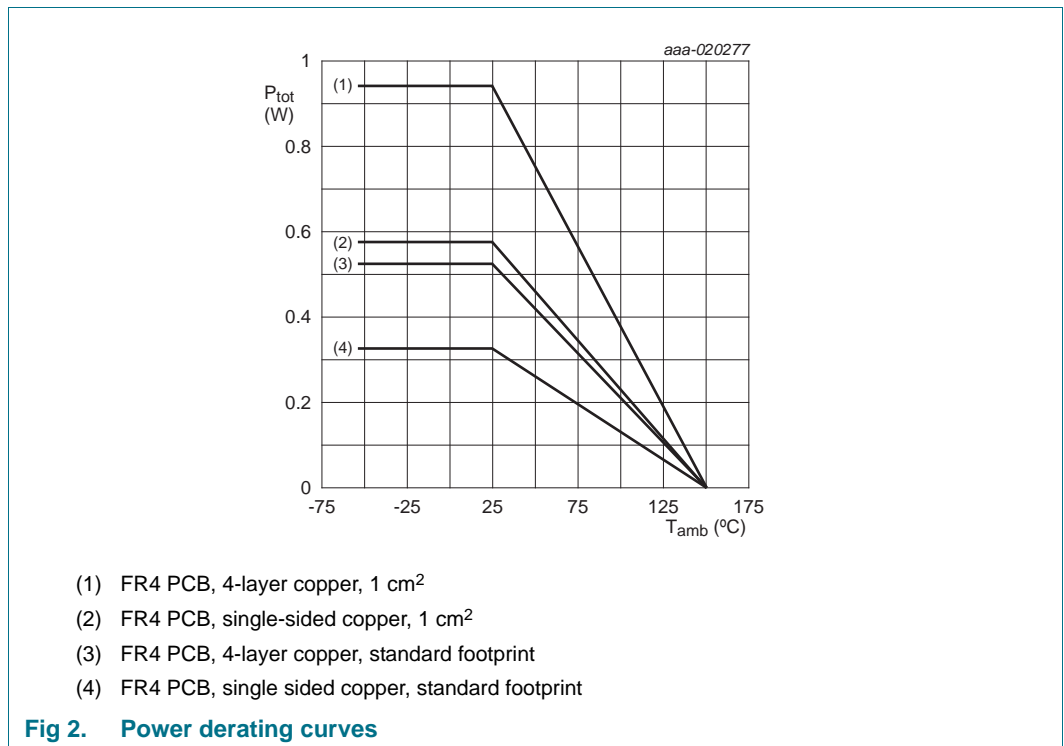
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V

Table 6. Limiting values ...continued
 In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _I	input voltage					
	PDTB113EQA		-10	+10	V	
	PDTB123EQA		-12	+10	V	
	PDTB143EQA		-30	+10	V	
	PDTB114EQA		-50	+10	V	
I _O	output current		-	-500	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
		[2]	-	575	mW	
		[3]	-	525	mW	
		[4]	-	940	mW	
T _j	junction temperature		-	150	°C	
T _{amb}	ambient temperature		-55	+150	°C	
T _{stg}	storage temperature		-65	+150	°C	

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².

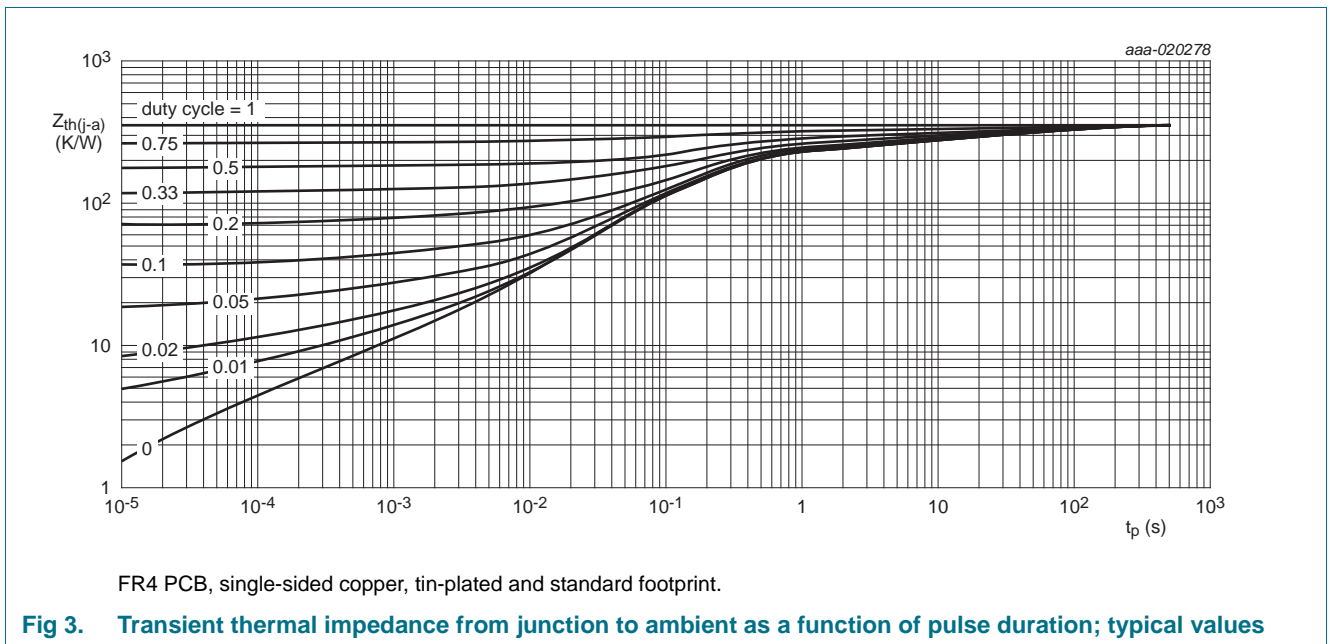


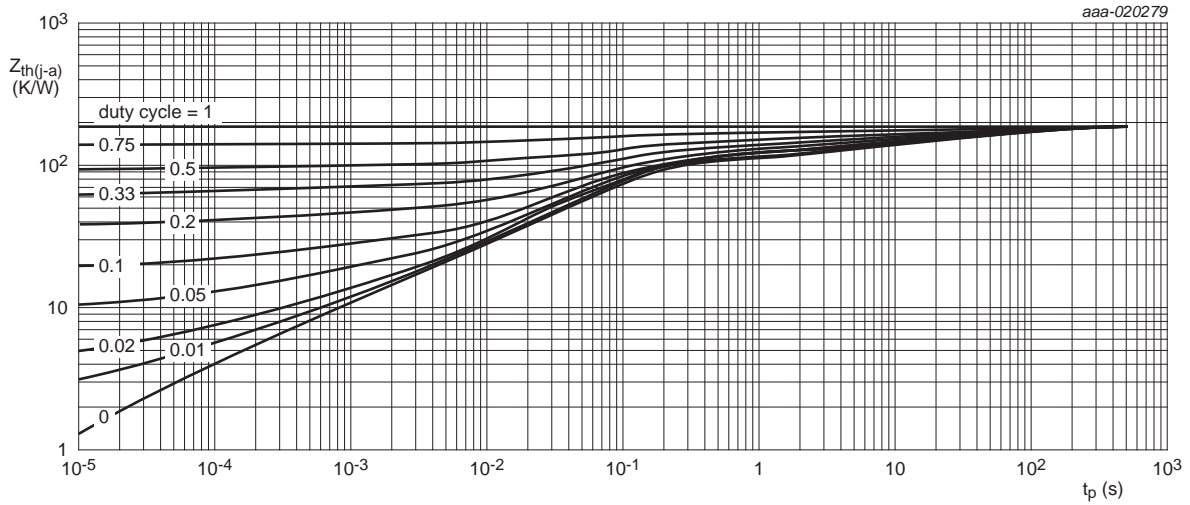
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
			[2]	-	-	218	K/W
			[3]	-	-	239	K/W
			[4]	-	-	133	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	40	K/W	

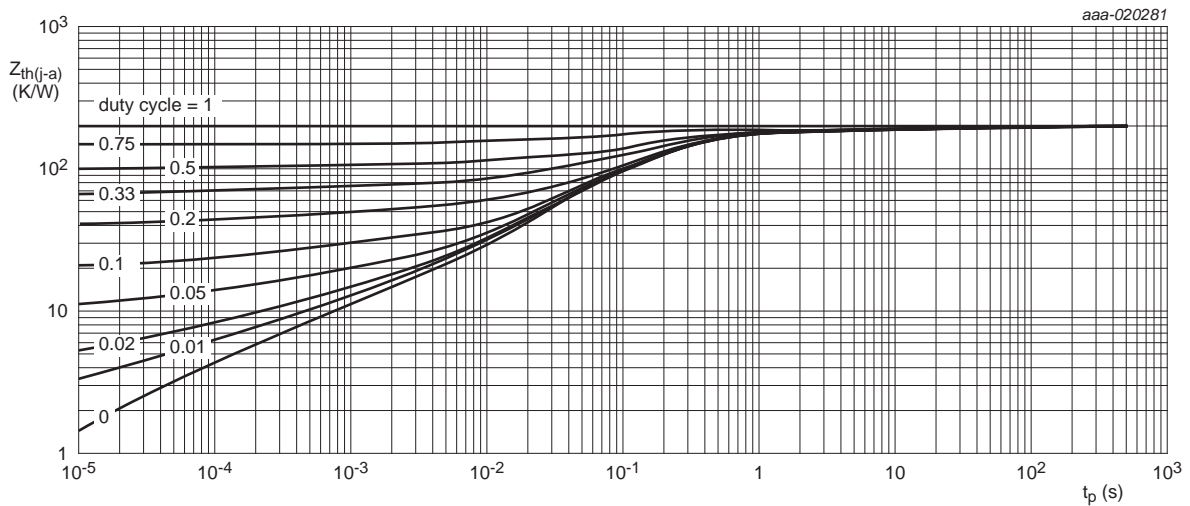
- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².





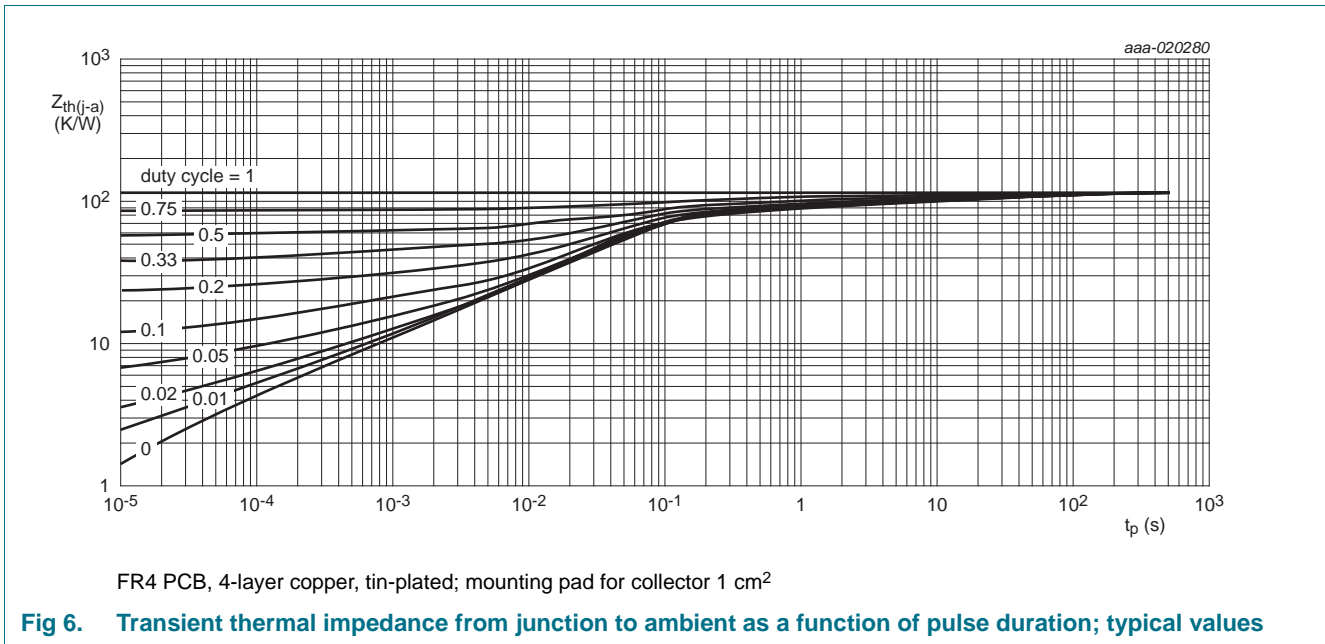
FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2 .

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

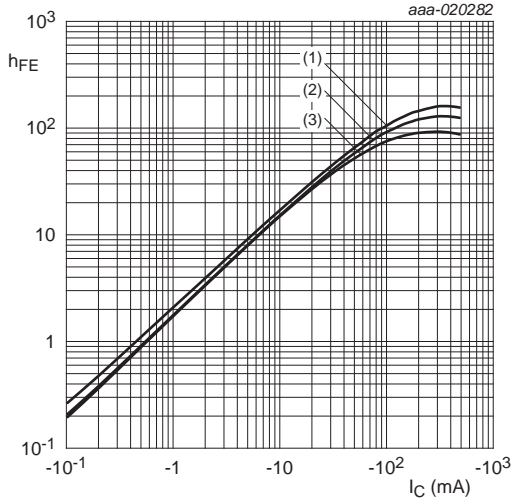
Table 8. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -50\text{ V}; I_B = 0\text{ A}$	-	-	-0.5	μA
I_{EBO}	emitter-base cut-off current					
	PDTB113EQA	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-4	mA
	PDTB123EQA		-	-	-2	mA
	PDTB143EQA		-	-	-0.9	mA
PDTB114EQA	-		-	-0.4	mA	
h_{FE}	DC current gain					
	PDTB113EQA	$V_{CE} = -5\text{ V}; I_C = -50\text{ mA}$	33	-	-	
	PDTB123EQA		40	-	-	
	PDTB143EQA		60	-	-	
PDTB114EQA	70		-	-		
V_{CEsat}	collector-emitter saturation voltage	$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage					
	PDTB113EQA	$V_{CE} = -5\text{ V}; I_C = -100\text{ }\mu\text{A}$	-0.6	-1.05	-1.5	V
	PDTB123EQA		-0.6	-1.05	-1.8	V
	PDTB143EQA		-0.6	-1.05	-1.5	V
PDTB114EQA	-0.6		-1.05	-1.5	V	
$V_{I(on)}$	on-state input voltage					
	PDTB113EQA	$V_{CE} = -0.3\text{ V}; I_C = -20\text{ mA}$	-1	-1.45	-1.8	V
	PDTB123EQA		-1	-1.5	-2	V
	PDTB143EQA		-1	-1.7	-2.2	V
PDTB114EQA	-1		-2.2	-3	V	
R1	bias resistor 1 (input)		[1]			
	PDTB113EQA		0.7	1	1.3	k Ω
	PDTB123EQA		1.54	2.2	2.86	k Ω
	PDTB143EQA		3.3	4.7	6.1	k Ω
	PDTB114EQA		7	10	13	k Ω
R2/R1	bias resistor ratio		[1]			
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	7	-	pF
f_T	transition frequency	$V_{CE} = -5\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	[2]			

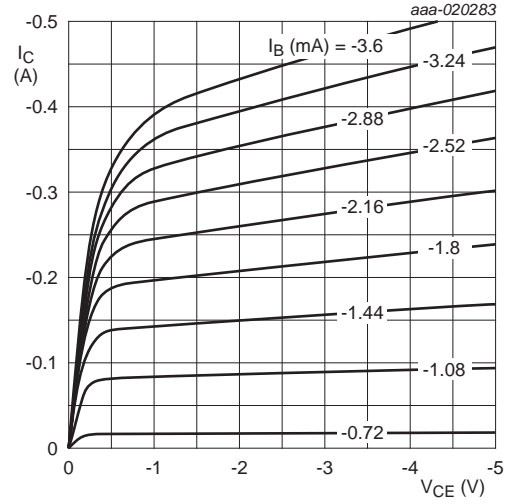
[1] See section test information for resistor calculation and test conditions.

[2] Characteristics of built-in transistor.



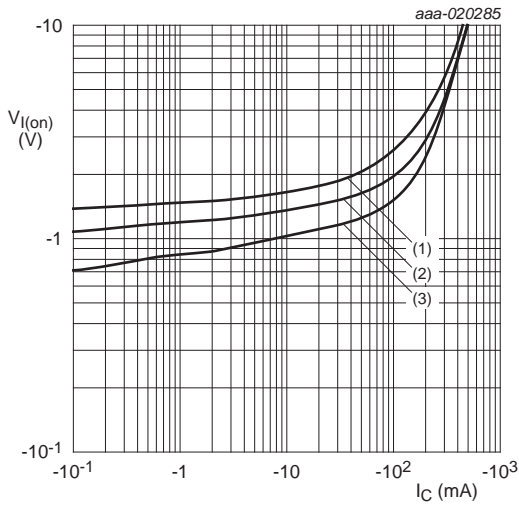
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 7. PDTB113EQA: DC current gain as a function of collector current; typical values



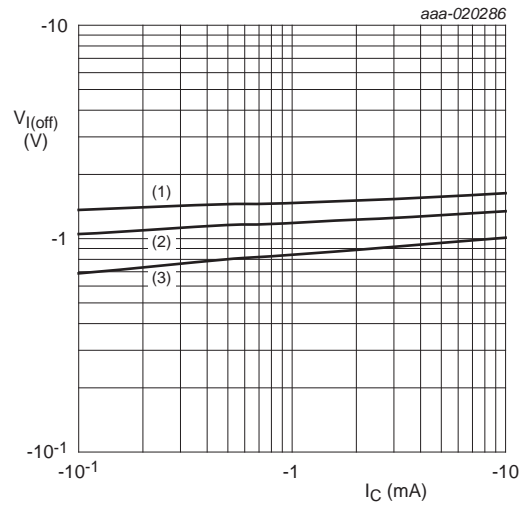
$T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 8. PDTB113EQA: Collector current as a function of collector-emitter voltage; typical values



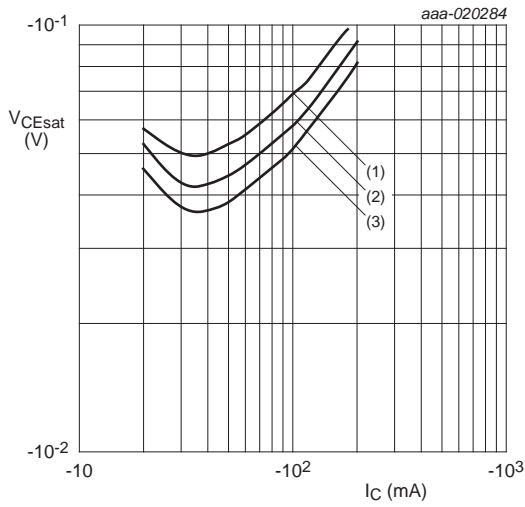
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 9. PDTB113EQA: On-state input voltage as a function of collector current; typical values



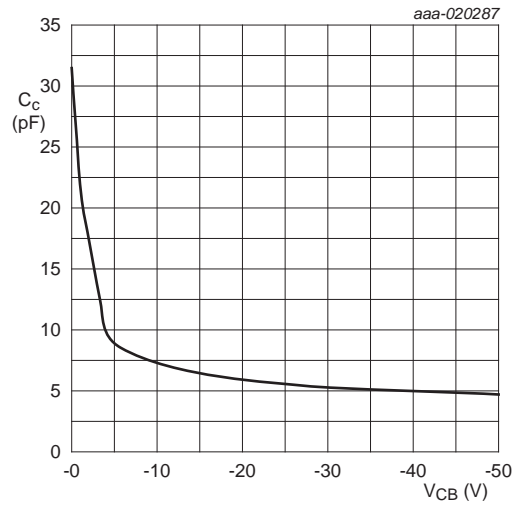
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 10. PDTB113EQA: Off-state input voltage as a function of collector current; typical values



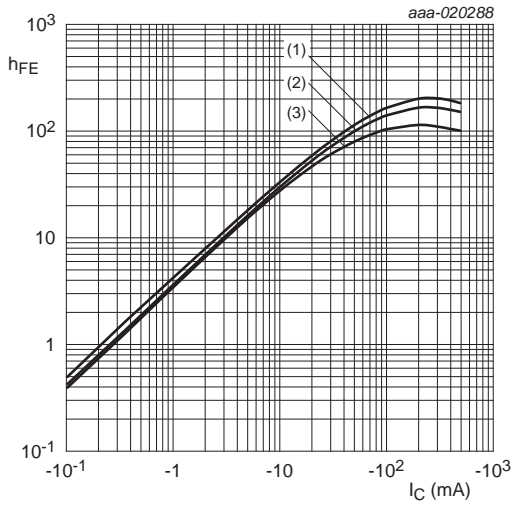
- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = -40\text{ °C}$

Fig 11. PDTB113EQA: Collector-emitter saturation voltage as a function of collector current; typical values



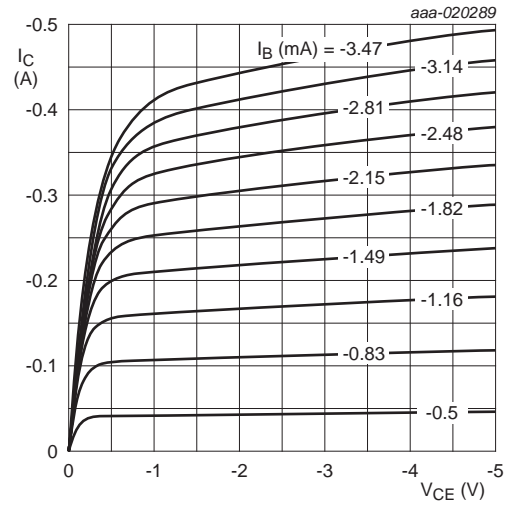
$f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$

Fig 12. PDTB113EQA: Collector capacitance as a function of collector-base voltage; typical values



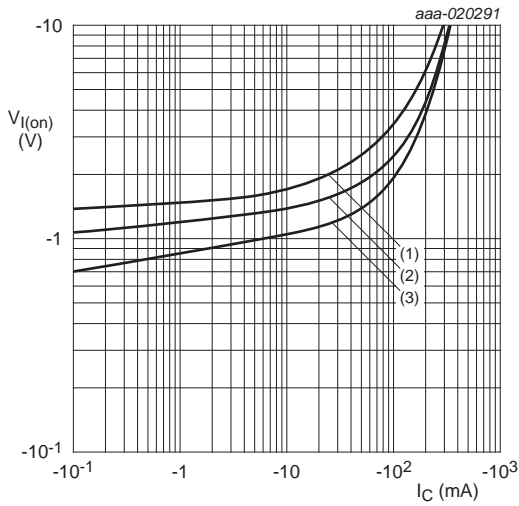
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 13. PDTB123EQA: DC current gain as a function of collector current; typical values



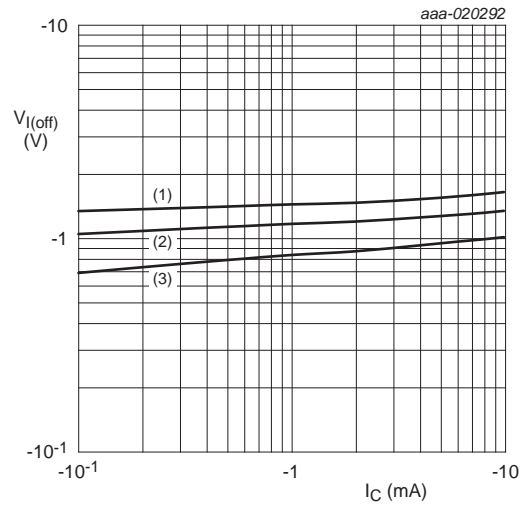
$T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 14. PDTB123EQA: Collector current as a function of collector-emitter voltage; typical values



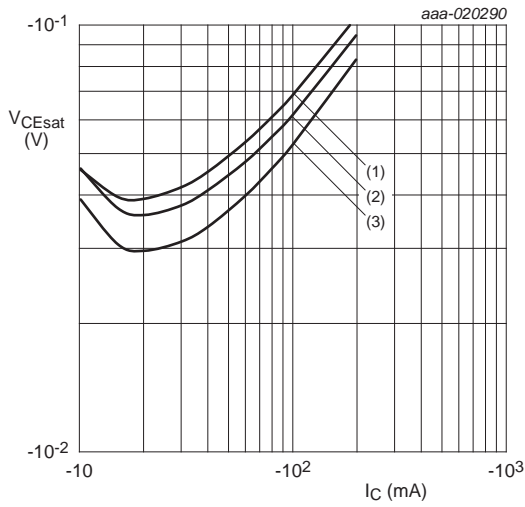
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 15. PDTB123EQA: On-state input voltage as a function of collector current; typical values



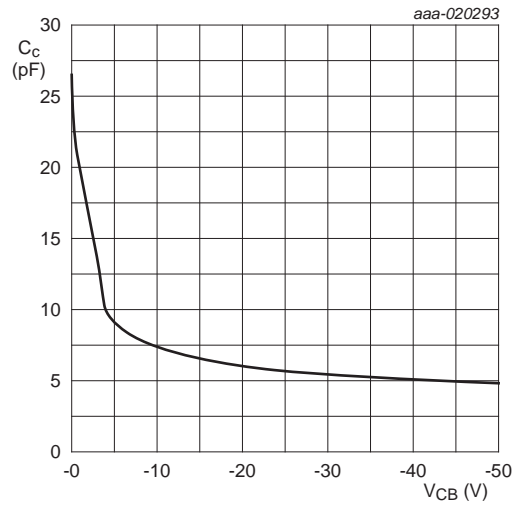
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 16. PDTB123EQA: Off-state input voltage as a function of collector current; typical values



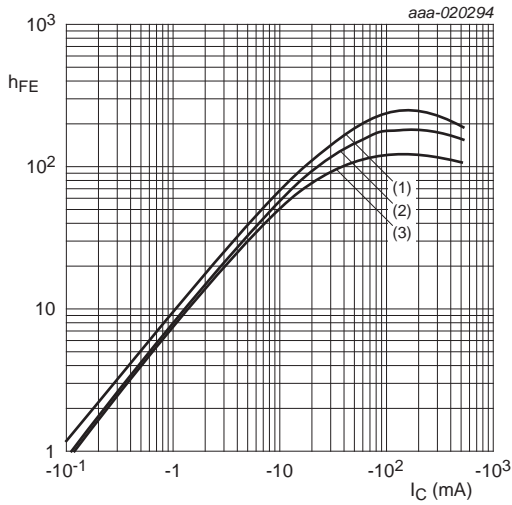
- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 - (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 - (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig 17. PDTB123EQA: Collector-emitter saturation voltage as a function of collector current; typical values



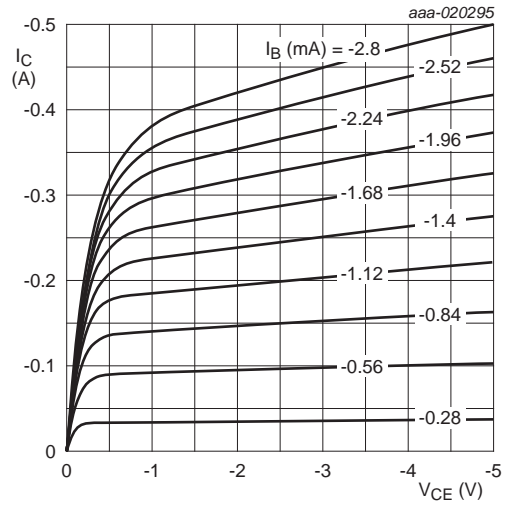
$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig 18. PDTB123EQA: Collector capacitance as a function of collector-base voltage; typical values



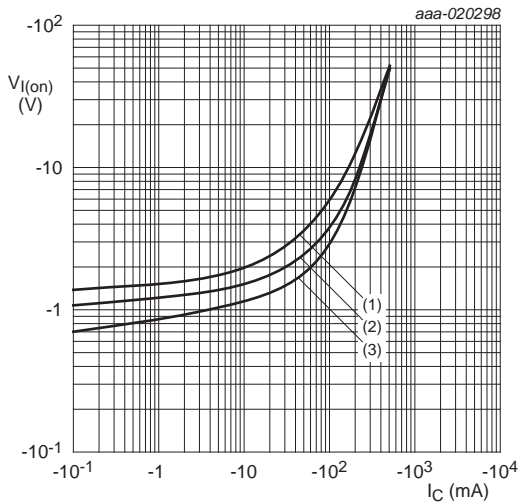
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 19. PDTB143EQA: DC current gain as a function of collector current; typical values



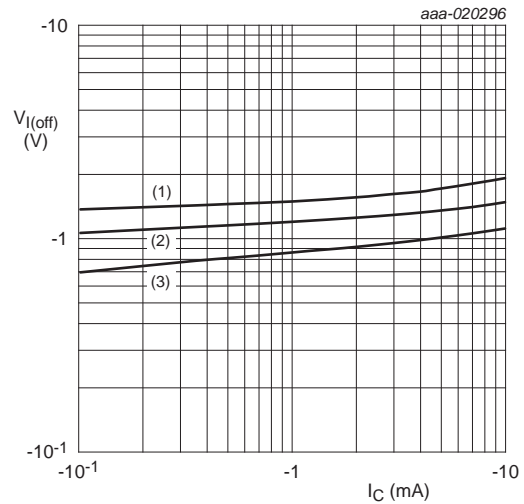
$T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 20. PDTB143EQA: Collector current as a function of collector-emitter voltage; typical values



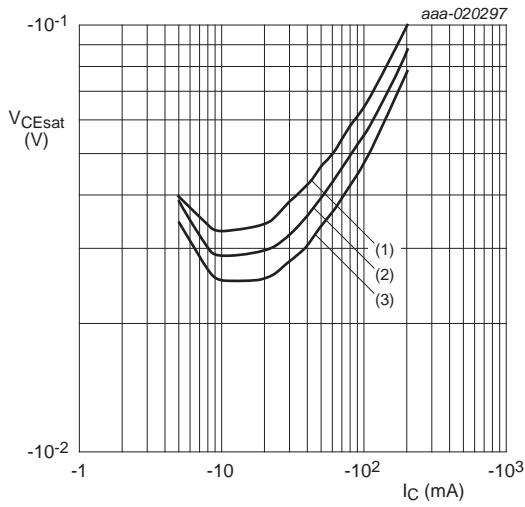
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 21. PDTB143EQA: On-state input voltage as a function of collector current; typical values



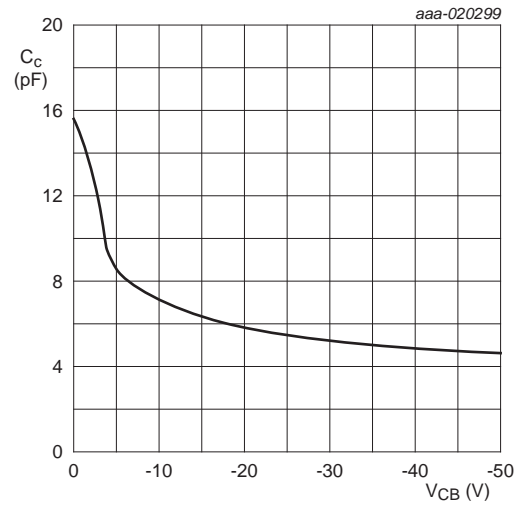
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 22. PDTB143EQA: Off-state input voltage as a function of collector current; typical values



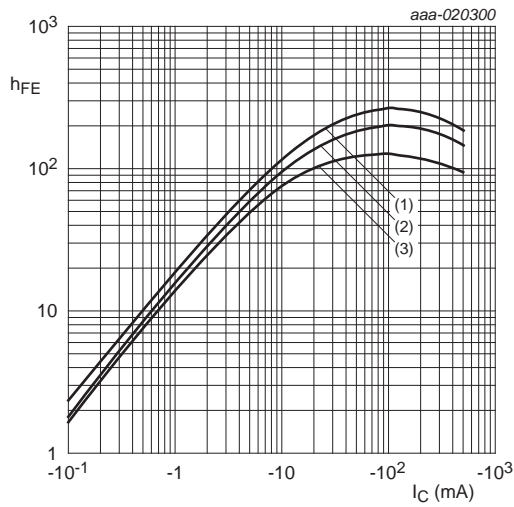
- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 - (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 - (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig 23. PDTB143EQA: Collector-emitter saturation voltage as a function of collector current; typical values



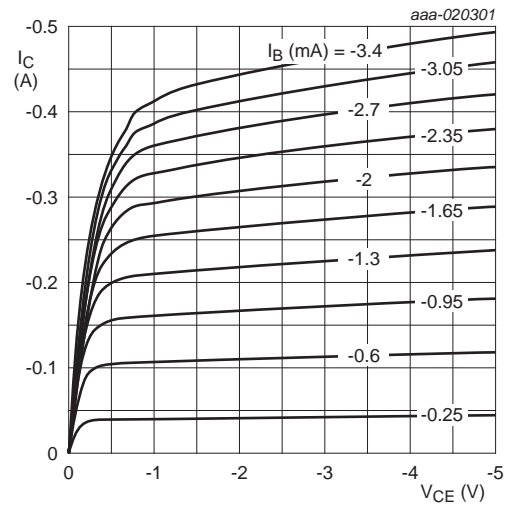
$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig 24. PDTB143EQA: Collector capacitance as a function of collector-base voltage; typical values



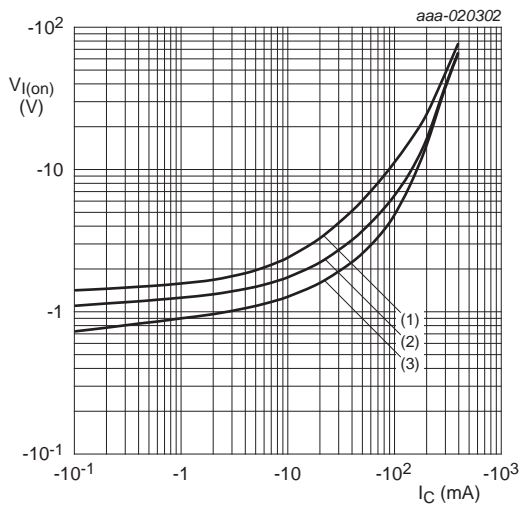
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 25. PDTB114EQA: DC current gain as a function of collector current; typical values



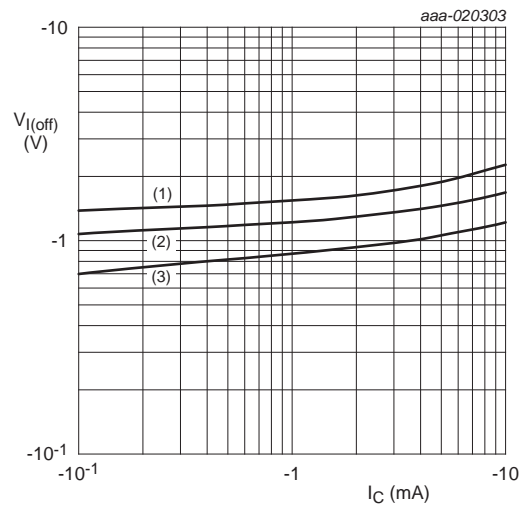
$T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 26. PDTB114EQA: Collector current as a function of collector-emitter voltage; typical values



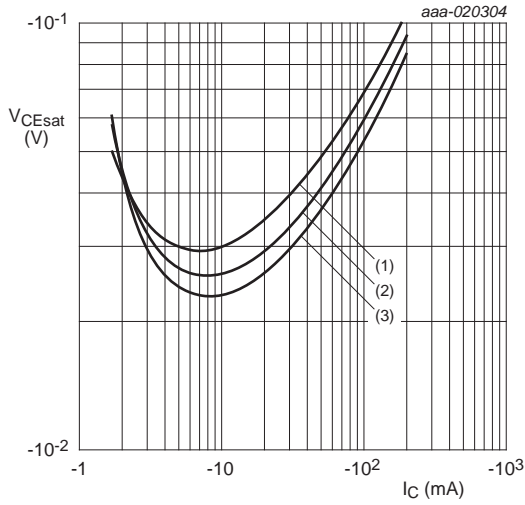
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 27. PDTB114EQA: On-state input voltage as a function of collector current; typical values



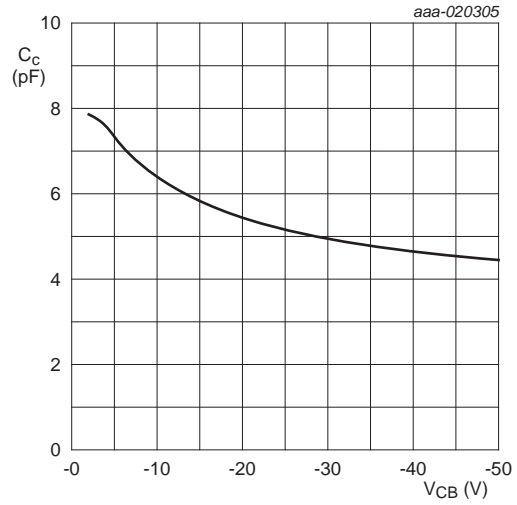
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 28. PDTB114EQA: Off-state input voltage as a function of collector current; typical values



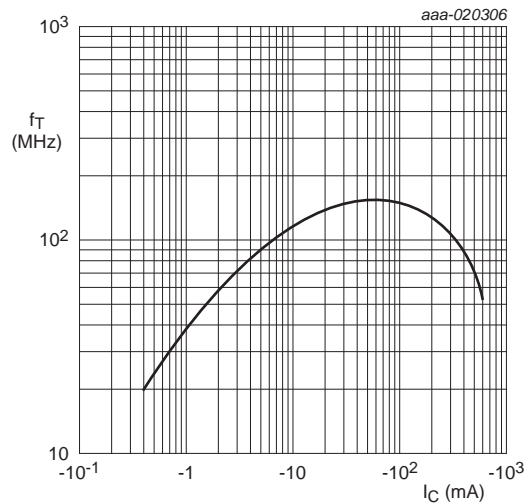
- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = -40\text{ °C}$

Fig 29. PDTB114EQA: Collector-emitter saturation voltage as a function of collector current; typical values



$f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$

Fig 30. PDTB114EQA: Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = -5\text{ V}; f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$

Fig 31. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

8.2 Resistor calculation

- Calculation of bias resistor 1 (R1):

$$R1 = \frac{V(I_{I2}) - V(I_{I1})}{I_{I2} - I_{I1}}$$

- Calculation method A of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I_{I3})}{R1 \cdot I_{I3}} - 1$$

- Calculation method B of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I_{I4}) - V(I_{I3})}{R1 \cdot (I_{I4} - I_{I3})} - 1$$

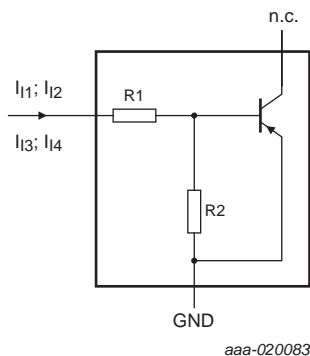


Fig 32. Resistor test circuit

8.3 Resistor test conditions

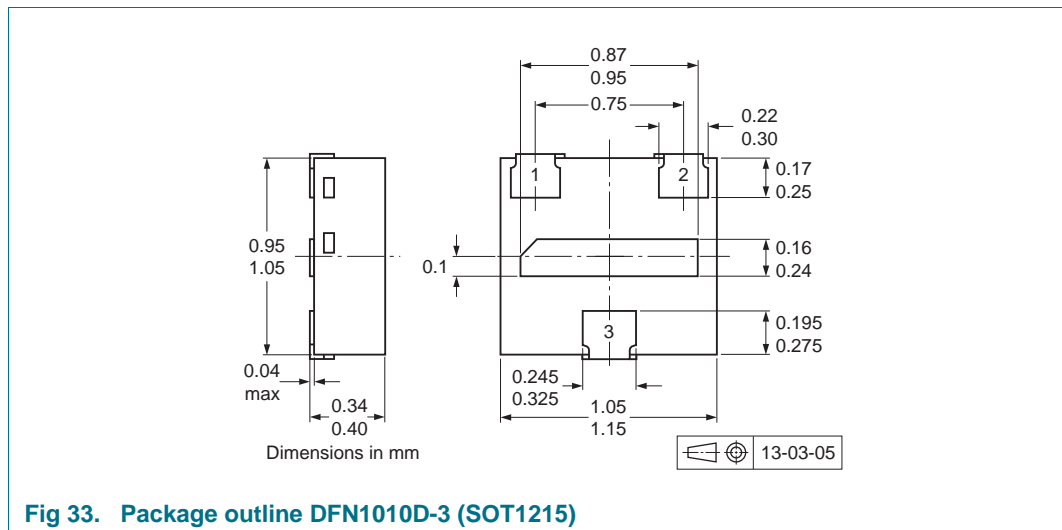
Table 9. Resistor test conditions

Type number		R1	R2	Test conditions			
		kΩ	kΩ	I _{I1}	I _{I2}	I _{I3}	I _{I4}
PDTB113EQA	[1]	1	1	-1.5 mA	-1.9 mA	2.20 mA	-
PDTB123EQA	[1]	2.2	2.2	-0.7 mA	-0.8 mA	0.75 mA	-
PDTB143EQA	[2]	4.7	4.7	-1.3 mA	-1.5 mA	1.05 mA	1.25 mA
PDTB114EQA	[2]	10	10	-0.7 mA	-0.8 mA	0.45 mA	0.55 mA

[1] Uses calculation method A of bias resistor ratio R2/R1

[2] Uses calculation method B of bias resistor ratio R2/R1

9. Package outline



10. Soldering

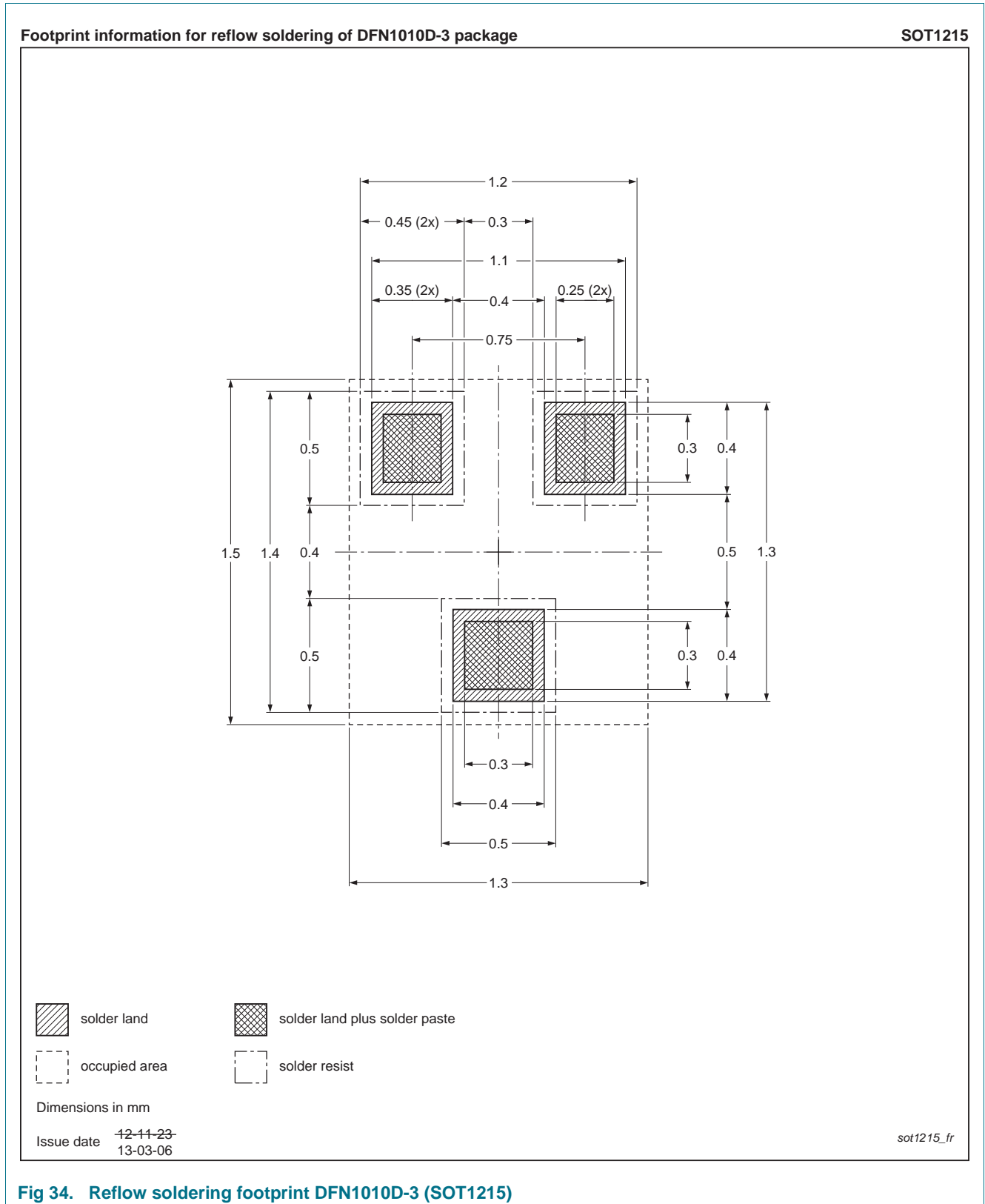


Fig 34. Reflow soldering footprint DFN1010D-3 (SOT1215)

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB113_123_143_114EQA_SER v.1	20160330	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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